

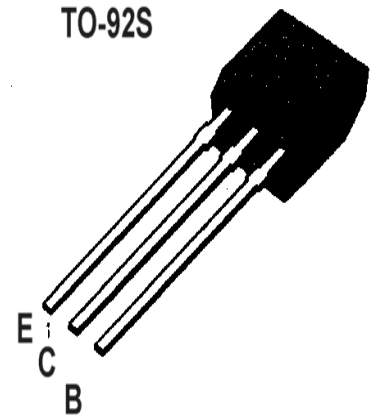
PNP Transistors

—PNP Silicon—

■■ APPLICATION: General Purpose Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-180	V
Collector-emitter voltage	V _{CEO}	-150	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-0.6	A
Collector Power Dissipation	P _C	0.3	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C, R_G=10Ω)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV _{CBO}	-180			V	I _C =-0.1mA	I _E =0	
Collector-Emitter Breakdown Voltage	BV _{CEO}	-150			V	I _C =-1mA	I _B =0	
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E =-0.1mA	I _C =0	
Collector Cut-off Current	I _{CBO}			-0.1	uA	V _{CB} =-120V	I _E =0	
Emitter Cut-off Current	I _{EBO}			-0.1	uA	V _{EB} =-3V	I _C =0	
Base-Emitter Saturation Voltage	V _{BE(sat)}			-1	V	I _C =-50mA	I _B =-5mA	
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.5	V	I _C =-50mA	I _B =-5mA	
DC Current Gain	H _{FE}	80			β	V _{CE} =-5V	I _C =-10mA	
Gain bandwidth product	f _T	200			MHz	V _{CE} =-20V	I _E =-50mA	f=100MHz
Common Base Output Capacitance	C _{ob}			6	pF	V _{CB} =-10V	I _E =0	f=1MHz
Noise Figure	NF			8	dB	V _{ce} =-5V, I _c =-0.25A, f=10Hz~15.7KHz, R _g =1KΩ		

■■ h_{FE} Classification And Marking

Print Mark	2N5401	
Classification	h _{FE}	80~150 100~250